Christian J Zollner

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	AlGaN Deep-Ultraviolet Light-Emitting Diodes Grown on SiC Substrates. ACS Photonics, 2020, 7, 554-561.	3.2	59
2	Fabrication technology for high light-extraction ultraviolet thin-film flip-chip (UV TFFC) LEDs grown on SiC. Semiconductor Science and Technology, 2019, 34, 035007.	1.0	33
3	Germicidal ultraviolet LEDs: a review of applications and semiconductor technologies. Semiconductor Science and Technology, 2021, 36, 123001.	1.0	32
4	Reduced dislocation density and residual tension in AlN grown on SiC by metalorganic chemical vapor deposition. Applied Physics Letters, 2019, 115, .	1.5	29
5	Low threading dislocation density aluminum nitride on silicon carbide through the use of reduced temperature interlayers. Journal of Crystal Growth, 2018, 483, 134-139.	0.7	20
6	Impact of roughening density on the light extraction efficiency of thin-film flip-chip ultraviolet LEDs grown on SiC. Optics Express, 2019, 27, A1074.	1.7	17
7	Growth of highly conductive Al-rich AlGaN:Si with low group-III vacancy concentration. AlP Advances, 2021, 11, .	0.6	13
8	Highly Conductive n-Al0.65Ga0.35N Grown by MOCVD Using Low V/III Ratio. Crystals, 2021, 11, 1006.	1.0	12
9	Superlattice hole injection layers for UV LEDs grown on SiC. Optical Materials Express, 2020, 10, 2171.	1.6	11
10	Developments in AlGaN and UV-C LEDs grown on SiC. , 2018, , .		8
11	Size dependent characteristics of AlGaN-based deep ultraviolet micro-light-emitting-diodes. Applied Physics Express, 2022, 15, 064003.	1.1	7
12	High conductivity n-Al _{0.6} Ga _{0.4} N by ammonia-assisted molecular beam epitaxy for buried tunnel junctions in UV emitters. Optics Express, 2021, 29, 40781.	1.7	5
13	Effect of nucleation layer thickness on reducing dislocation density in AlN layer for AlGaN-based UVC LED. Microelectronics International, 2021, 38, 113-118.	0.4	1